TSB94T100S(A)S-255A

10A/100V(1), low VF Schottky barrier diode with trench MOS structure

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2388 μm	94 mil
	Top Metal Pad Size (B)	2286μm	90mil
	Chip Size (C)	2311μm	91mil
	Wafer Thickness (D)	240 μm	9.5 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	TSB94T100SS-255A	Al/Ag
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23℃±3℃)	

Electrical Characteristics (TJ=25℃, unless otherwise specified)(2)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	105	109	-	V	I_R =100μA
V_F	Instantaneous Forward Voltage	-	0.69	0.71	V	I_F =15A(3)
I_R	Reverse Leakage Current	-	18	40	μA	V_R =102V
T_J, T_{STG}	Operating and Storage Temperature	-40℃ to 150℃ Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assumes the dies are assembled in DO-201 packages. Actual performance may degrade when assembled. YJ does not guarantee device performance after assembly;

(3) Pulse Width tp = < 300μS, Duty Cycle <2%;